

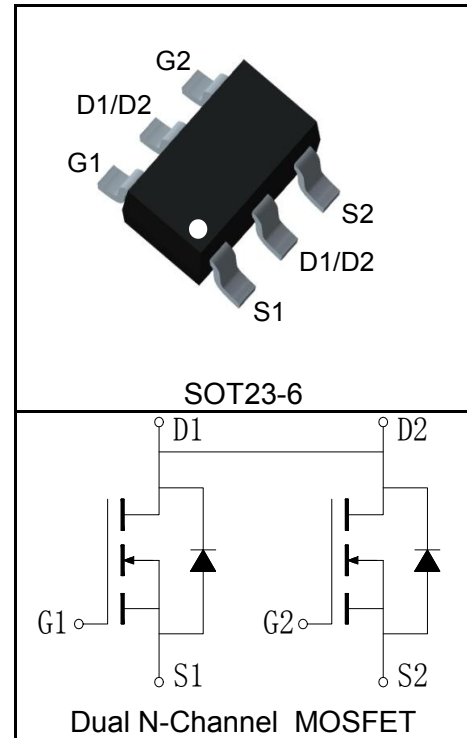
Features

- 20V/6A,
 $R_{DS(ON)} = 18m\Omega(Typ.)@V_{GS}=4.5V$
 $R_{DS(ON)} = 23m\Omega(Typ.)@V_{GS}=2.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Power Management

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$ 1.7	A
Mounted on Large Heat Sink			
$I_{DP}^{(1)}$	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ 24	A
$I_D^{(2)}$	Continuous Drain Current($V_{GS}=4.5V$)	$T_A=25^\circ\text{C}$ 6	A
		$T_A=70^\circ\text{C}$ 4.5	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 1.25	W
		$T_A=70^\circ\text{C}$ 0.75	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	-	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C}/\text{W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	TBD	mJ

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

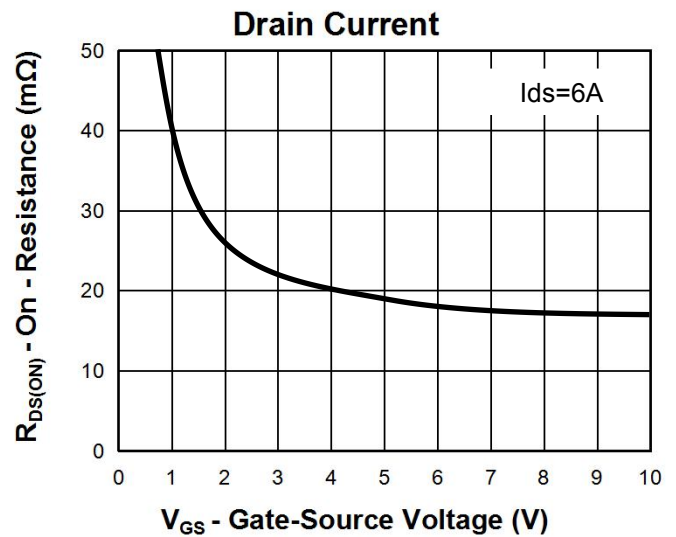
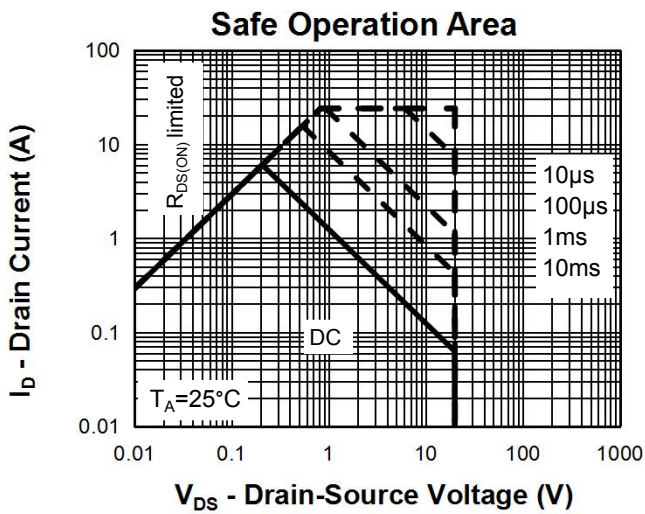
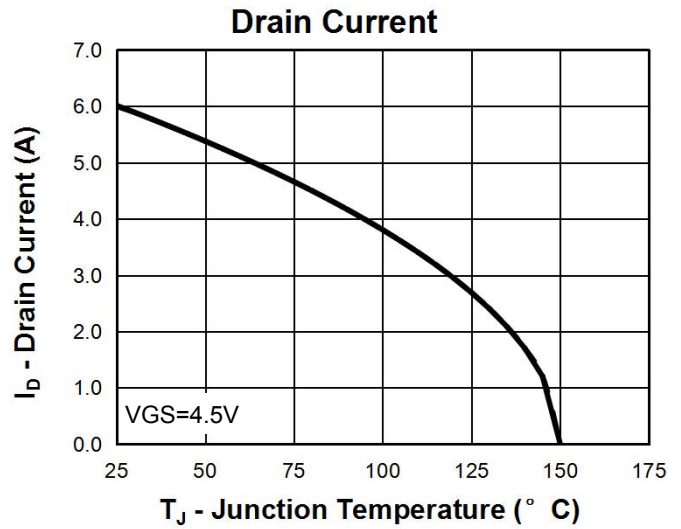
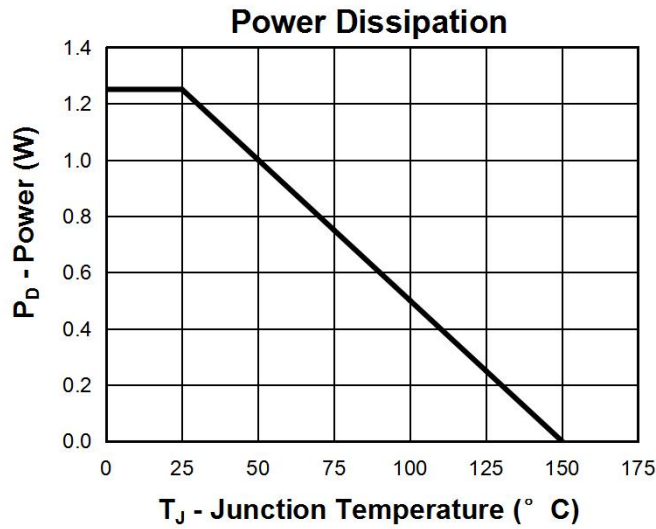
Symbol	Parameter	Test Condition	RU8205C6			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	0.5	0.7	1.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=6A$		18	22	$m\Omega$
		$V_{GS}=2.5V, I_{DS}=5A$		23	28	$m\Omega$
Diode Characteristics						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$			1	V
t_{rr}	Reverse Recovery Time	$I_{SD}=1A, di_{SD}/dt=100A/\mu s$		15		ns
Q_{rr}	Reverse Recovery Charge			8		nC
Dynamic Characteristics⁽⁶⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.5		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=10V,$ Frequency=1.0MHz		590		pF
C_{oss}	Output Capacitance			125		
C_{rss}	Reverse Transfer Capacitance			90		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=10V, I_{DS}=6A,$ $V_{GEN}=4.5V, R_G=6\Omega$		8		ns
t_r	Turn-on Rise Time			15		
$t_{d(OFF)}$	Turn-off Delay Time			33		
t_f	Turn-off Fall Time			13		
Gate Charge Characteristics⁽⁶⁾						
Q_g	Total Gate Charge	$V_{DS}=16V, V_{GS}=4.5V,$ $I_{DS}=6A$		10		nC
Q_{gs}	Gate-Source Charge			1.6		
Q_{gd}	Gate-Drain Charge			3.4		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} . Starting $T_J = 25^\circ\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

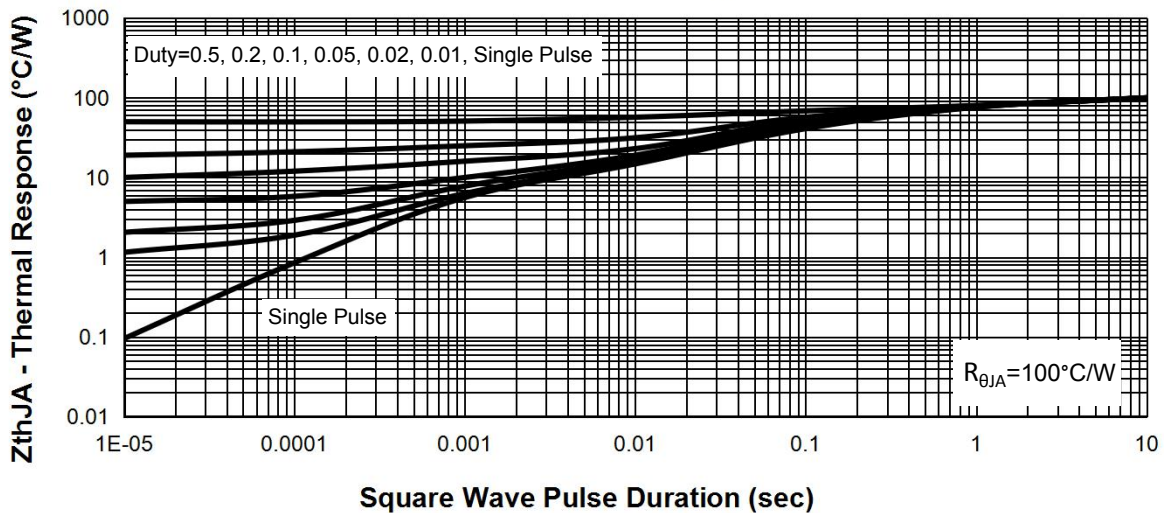
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU8205C6	RU8205A	SOT23-6	Tape&Reel	3000	7"	8mm

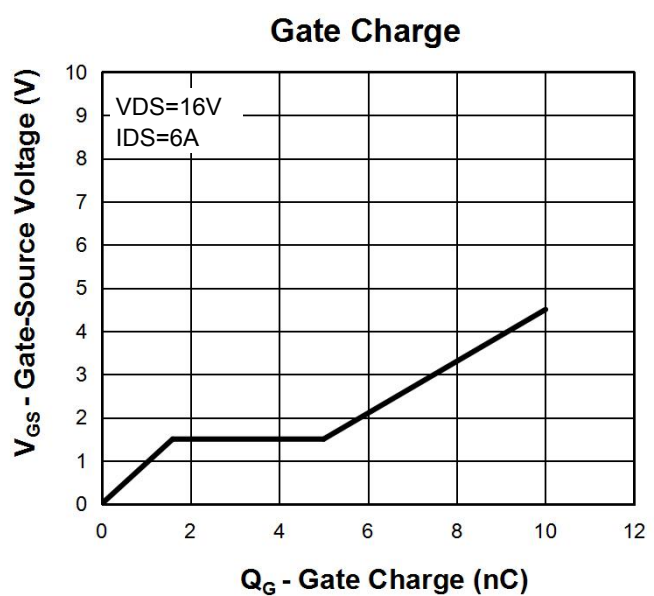
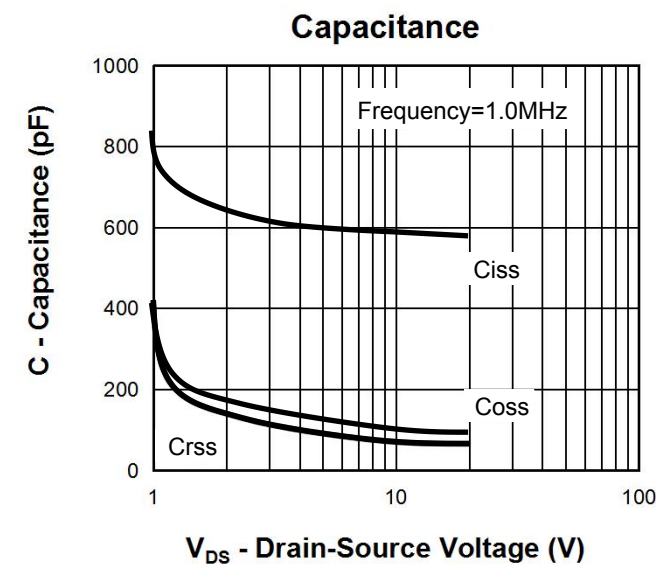
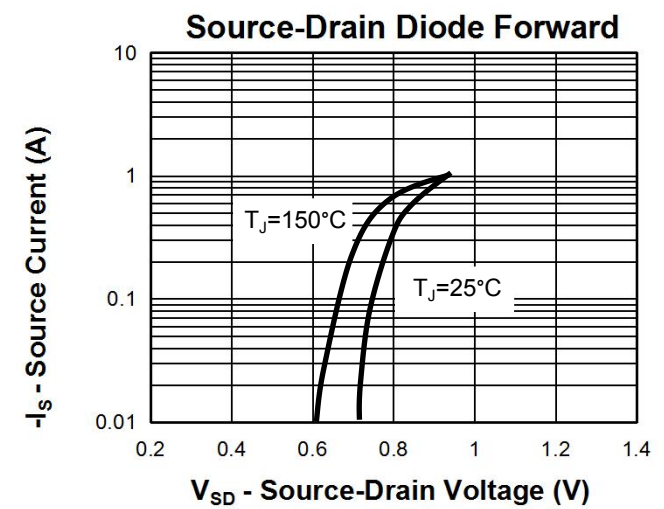
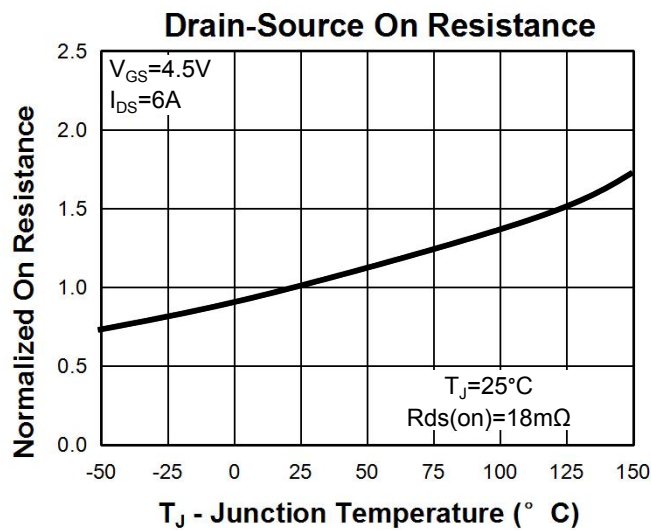
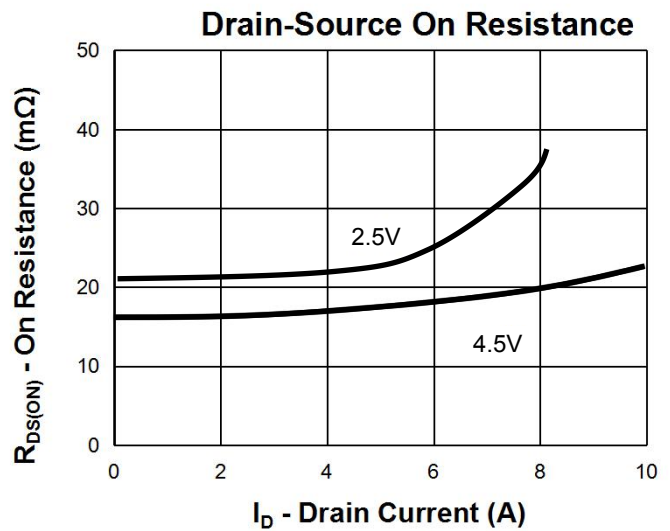
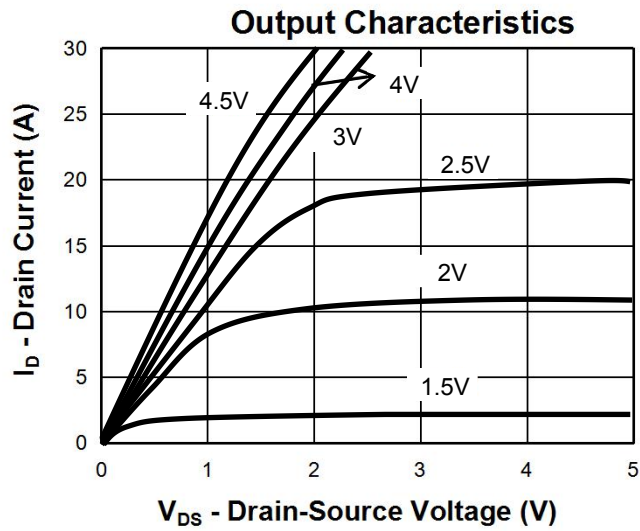
Typical Characteristics



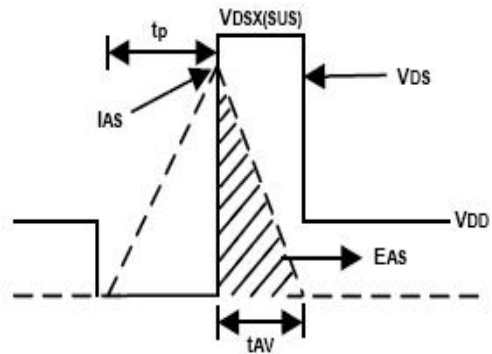
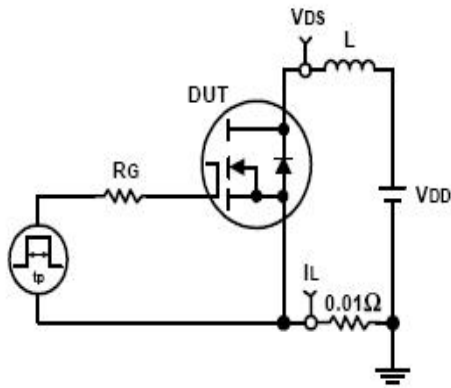
Thermal Transient Impedance



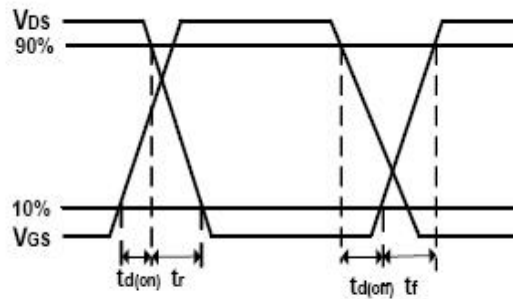
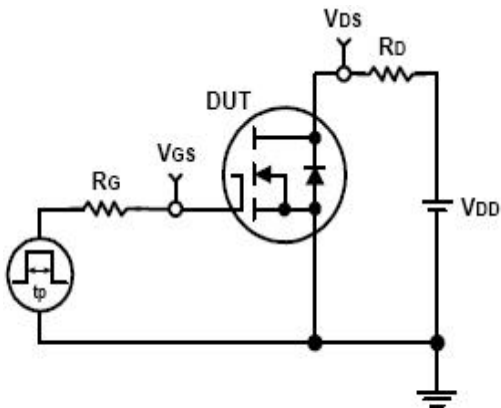
Typical Characteristics



Avalanche Test Circuit and Waveforms

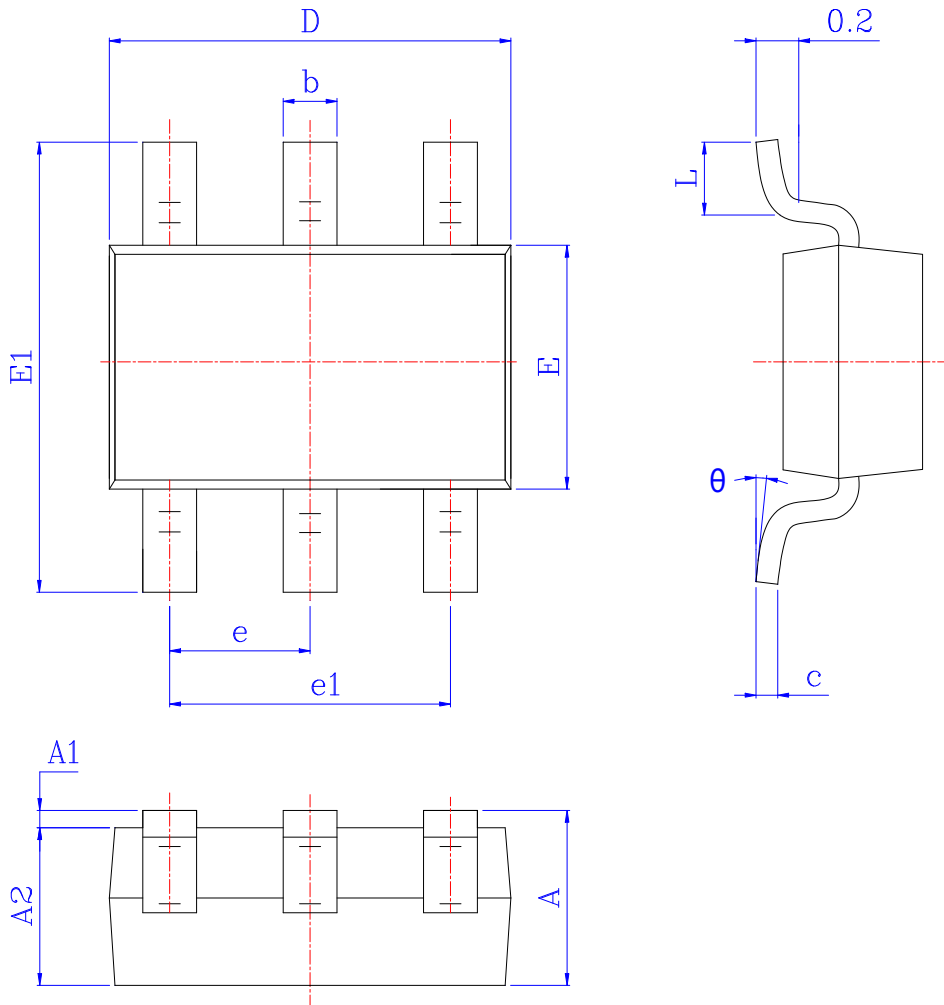


Switching Time Test Circuit and Waveforms



Package Information

SOT23-6



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.150	1.450	0.037	0.045	0.057
A1	0.000	0.060	0.150	0.000	0.002	0.006
A2	0.900	1.100	1.300	0.035	0.043	0.051
b	0.300	0.400	0.500	0.012	0.016	0.020
c	0.080	0.140	0.200	0.003	0.006	0.008
D	2.800	2.900	3.050	0.110	0.114	0.120
E	1.500	1.600	1.750	0.059	0.063	0.069
E1	2.600	2.800	3.000	0.102	0.110	0.118
e	0.950BSC			0.037BSC		
e1	1.800	1.900	2.000	0.071	0.075	0.079
L	0.300	0.450	0.600	0.012	0.018	0.024
θ	0°	4°	8°	0°	4°	8°

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[STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#) [BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#)
[IRF40SC240ARMA1](#)